

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
22 March 2001 (22.03.2001)

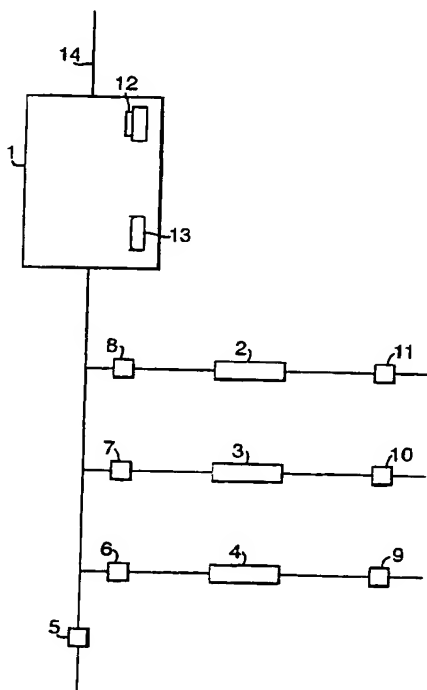
PCT

(10) International Publication Number
WO 01/20687 A1

- (51) International Patent Classification?: H01L 31/18, C30B 25/02, 29/48 (72) Inventor: STEVENSON, John (deceased).
- (21) International Application Number: PCT/GB00/03249 (72) Inventors; and
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- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data: 9921639.2 15 September 1999 (15.09.1999) GB
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- (81) Designated States (national): GB, JP, KR, US.

[Continued on next page]

(54) Title: NEW METHODS OF FABRICATING DEVICES AND SEMICONDUCTOR LAYERS COMPRISING CADMIUM MERCURY TELLURIDE, MERCURY TELLURIDE, AND CADMIUM TELLURIDE



(57) Abstract: The invention relates to a method of depositing $Hg_{1-x}Cd_xTe$ onto a substrate, in a MOVPE technique, where $0 \leq x \leq 1$; comprising the step of reacting together a volatile organotellurium compound, and one or both of (i) a volatile organocadmium compound and (ii) mercury vapour; characterised in that the organotellurium compound is isopropylallyltelluride. The invention also relates to devices, such as infrared sensors and solar cells, that comprise $Hg_{1-x}Cd_xTe$ materials.

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